

Dual N-channel 60 V, 10 mΩ standard level MOSFET

2 September 2015

Product data sheet

## 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	40	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	64	W
Static charact	eristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	8	10	mΩ
Dynamic char	acteristics FET1 and FE	T2					
Q <sub>GD</sub>	gate-drain charge	$I_{D} = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	9.7	-	nC

[1] Continuous current is limited by package.

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

# 6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
BUK7K13-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205					

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K13-60E	71360E

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	64	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	40	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>		-	38	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	213	А
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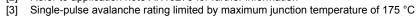
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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	diode FET1 and FET2	-	1			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	40	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	213	А
Avalanche Ru	uggedness FET1 and FET2		1			
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 40 \; {\sf A};  {\sf V}_{\sf sup} \le 60 \; {\sf V};  {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 10 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {\rm ^{\circ}C}; \; {\sf unclamped}; \\ & {\sf Fig. 4} \end{split}$	[2][3]	-	82	mJ

[1] Continuous current is limited by package.

[2] Refer to application note AN10273 for further information



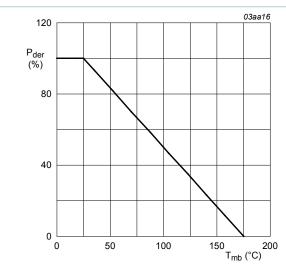
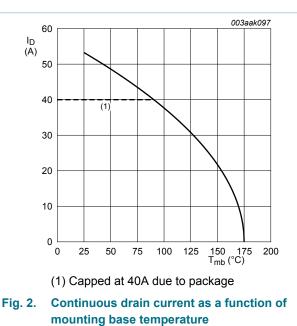


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

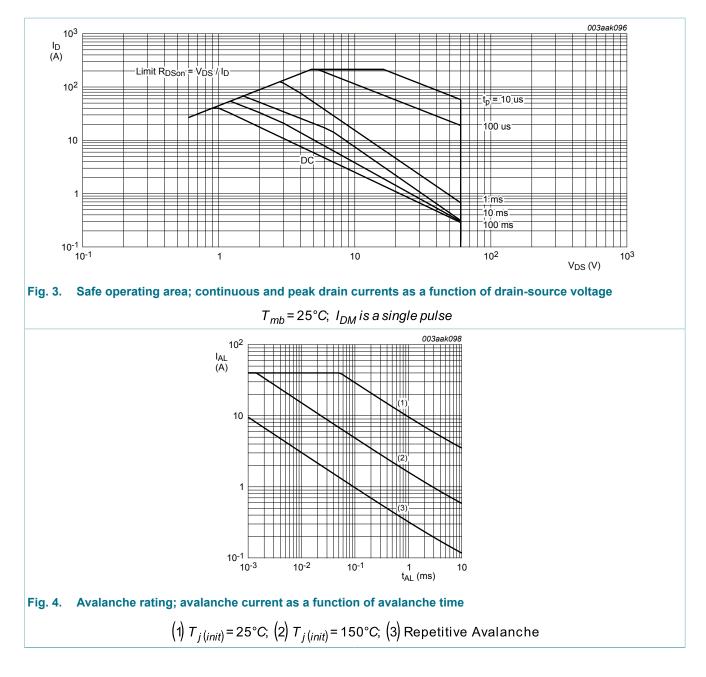
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



V<sub>GS</sub>≥10V

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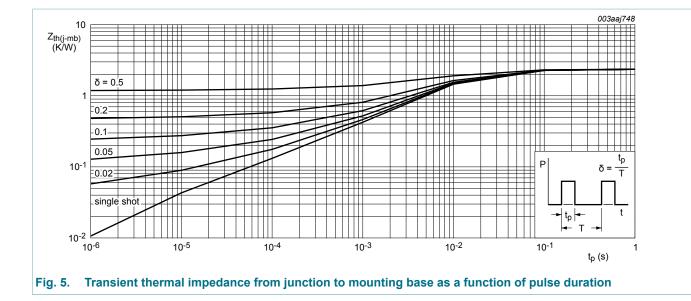
## 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.36	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

#### Table 6. Thermal characteristics

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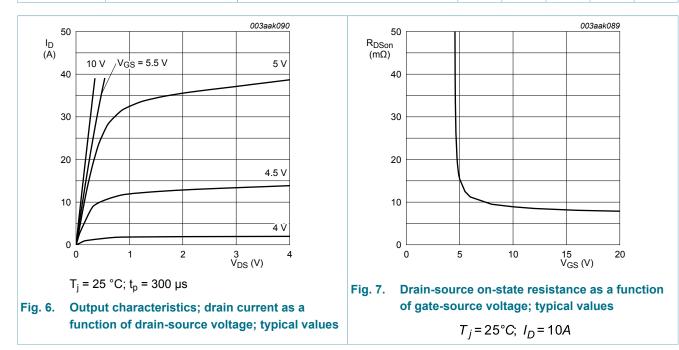
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2	· · ·				_
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I <sub>DSS</sub>	DSS drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA
		$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; Fig. 11	-	8	10	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	18	22	mΩ
Dynamic ch	naracteristics FET1 and FE	T2				
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 10 A; $V_{DS}$ = 48 V; $V_{GS}$ = 10 V;	-	30.1	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	6.7	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	9.7	-	nC

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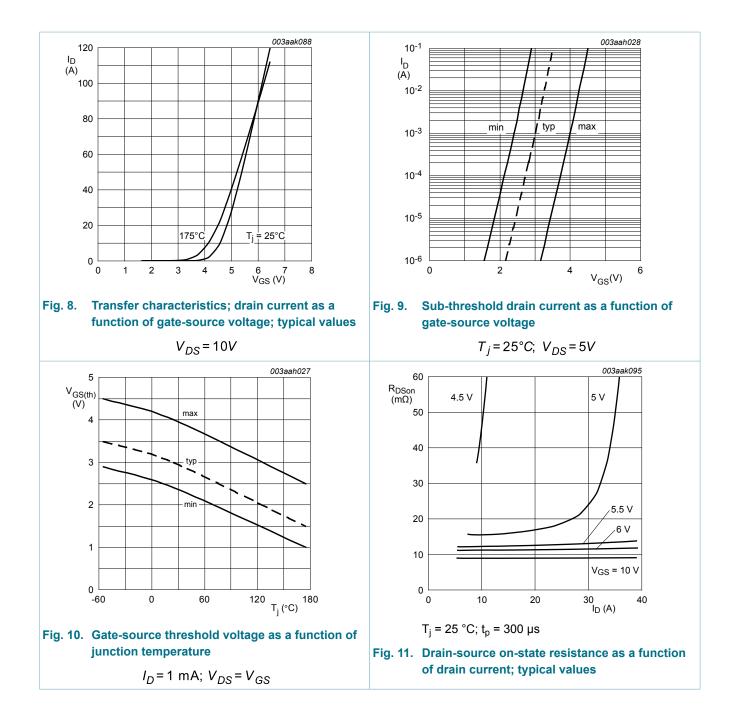
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>i</sub> = 25 °C; Fig. 15		-	1622	2163	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	229	275	pF
C <sub>rss</sub>	reverse transfer capacitance			-	143	196	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 48 \text{ V}; \text{ R}_{L} = 5 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	8.4	-	ns
t <sub>r</sub>	rise time			-	11.4	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	20.4	-	ns
t <sub>f</sub>	fall time			-	13.6	-	ns
Source-drai	in diode FET1 and FET2	·	1				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 10 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 10 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	25.6	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C		-	23.5	-	nC

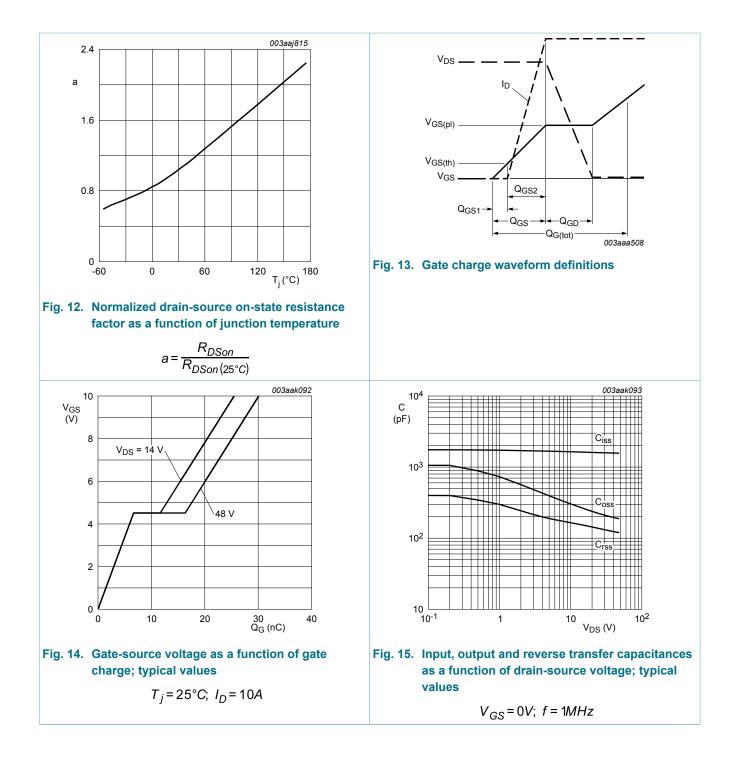


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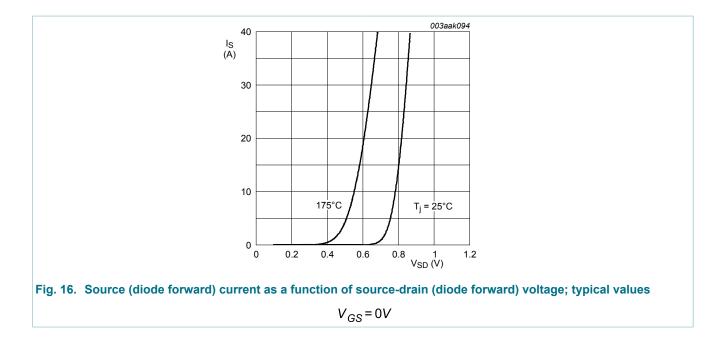


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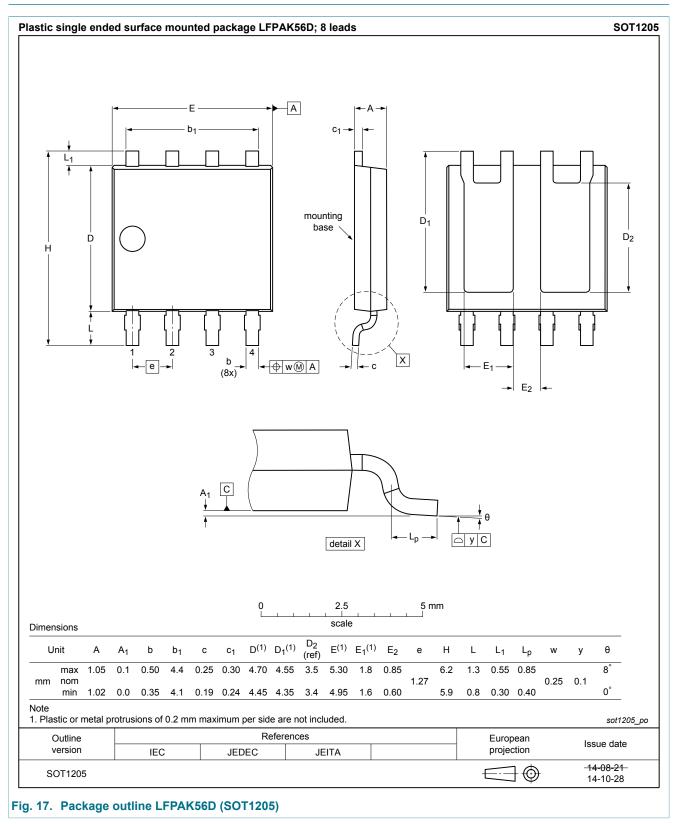
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## **11. Package outline**



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Product data sheet

#### Dual N-channel 60 V, 10 mΩ standard level MOSFET

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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